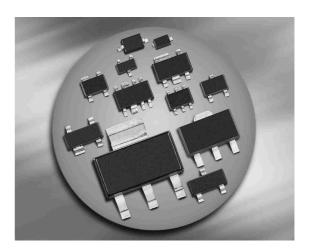
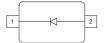


Silicon Tuning Diode

- For VHF 2-Band-hyperband-TV-tuners
- Very high capacitance ratio
- Low series resistance
- Excellent uniformity and matching due to "in-line" matching assembly procedure



BB669 BB689 BB689-02V



Туре	Package	Configuration	L _S (nH)	Marking
BB669	SOD323	single	1.8	1
BB689	SCD80	single	0.6	EE
BB689-02V	SC79	Single	0.6	E

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	30	V
Peak reverse voltage	V _{RM}	35	
($R \leq 5 \mathrm{k}\Omega$)			
Forward current	I _F	20	mA
Operating temperature range		-55 150	°C
Storage temperature	T _{stg}	-55 150	



Parameter	Symbol		Values		Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current	I _R				nA
V_{R} = 30 V		-	-	10	
V _R = 30 V, <i>T</i> _A = 85 °C		-	-	200	

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

Electrical Characteristics at $T_A = 25^{\circ}C$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Diode capacitance	CT				pF
V _R = 1 V, <i>f</i> = 1 MHz		51	56.5	61.5	
$V_{\rm R}$ = 2 V, <i>f</i> = 1 MHz		39.6	43.4	47.2	
V _R = 25 V, <i>f</i> = 1 MHz		2.6	2.8	3	
V _R = 28 V, <i>f</i> = 1 MHz		2.5	2.7	2.9	
Capacitance ratio	C _{T1} /C _{T28}	18	20.9	23.2	-
$V_{\rm R}$ = 1 V, $V_{\rm R}$ = 28 V, f = 1 MHz					
Capacitance ratio	C _{T2} /C _{T25}	14.5	15.5	17	
V _R = 2 V, V _R = 25 V, <i>f</i> = 1 MHz					
Capacitance matching ¹⁾	$\Delta C_{T}/C_{T}$	-	-	2	%
V _R = 1 V, V _R = 28 V, <i>f</i> = 1 MHz					
Series resistance	r _S	_	0.85	-	Ω
V _R = 8 V, <i>f</i> = 470 MHz					

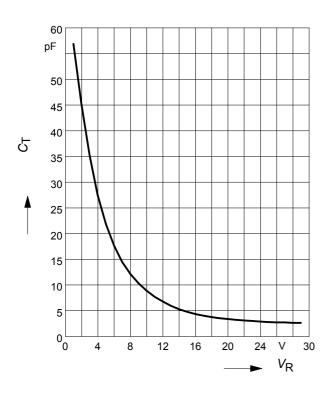
¹For details please refer to Application Note 047



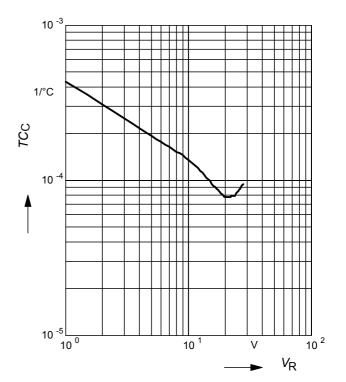


Diode capacitance $C_{T} = f(V_{R})$

f = 1 MHz

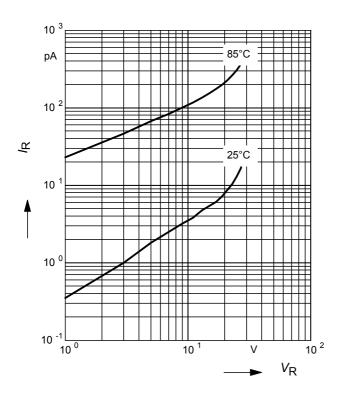


Temperature coefficient of the diode capacitance $T_{Cc} = f(V_R)$



Reverse current $I_{R} = f(V_{R})$

 T_A = Parameter



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